Product data sheet

1. General description

P-channel enhancement mode Field-Effect Transistor (FET) in a small SOT23 (TO-236AB) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

2. Features and benefits

- Trench MOSFET technology
- Low threshold voltage
- Very fast switching
- Enhanced power dissipation capability: Ptot = 980 mW
- ElectroStatic Discharge (ESD) protection 2 kV HBM

3. Applications

- LED driver
- Power management
- · High-side loadswitch
- Switching circuits

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V _{DS}	drain-source voltage	T _j = 25 °C		-	-	-20	V
V_{GS}	gate-source voltage			-8	-	8	V
I _D	drain current	$V_{GS} = -4.5 \text{ V}; T_{amb} = 25 \text{ °C}; t \le 5 \text{ s}$	[1]	-	-	-5.6	Α
Static characteristics							
R _{DSon}	drain-source on-state resistance	V_{GS} = -4.5 V; I_D = -4.5 A; T_j = 25 °C		-	27	32	mΩ

^[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 6 cm².





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5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate	<u> </u>	D I
2	S	source		
3	D	drain	1	G S 017aaa259

6. Ordering information

Table 3. Ordering information

Type number	Package	ckage				
	Name	Description	Version			
PMV27UPE	TO-236AB	plastic surface-mounted package; 3 leads	SOT23			

7. Marking

Table 4. Marking codes

Type number	Marking code [1]
PMV27UPE	%KD

^{[1] % =} placeholder for manufacturing site code

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V _{DS}	drain-source voltage	T _j = 25 °C		-	-20	V
V_{GS}	gate-source voltage			-8	8	V
I _D	drain current	V_{GS} = -4.5 V; T_{amb} = 25 °C; $t \le 5$ s	[1]	-	-5.6	Α
		V _{GS} = -4.5 V; T _{amb} = 25 °C	[1]	-	-4.5	Α
		V _{GS} = -4.5 V; T _{amb} = 100 °C	[1]	-	-2.8	Α
I _{DM}	peak drain current	T_{amb} = 25 °C; single pulse; $t_p \le 10$ μs		-	-18	Α
P _{tot}	total power dissipation	T _{amb} = 25 °C	<u>[2]</u>	-	490	mW

PMV27UPE

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Symbol	Parameter	Conditions		Min	Max	Unit
			[1]	-	980	mW
		T _{sp} = 25 °C		-	4150	mW
T _j	junction temperature			-55	150	°C
T _{amb}	ambient temperature			-55	150	°C
T _{stg}	storage temperature			-65	150	°C
Source-drain diode						
Is	source current	T _{amb} = 25 °C	[1]	-	-1.2	Α

- [1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 6 cm².
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

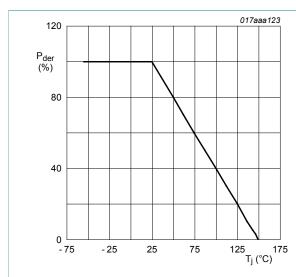
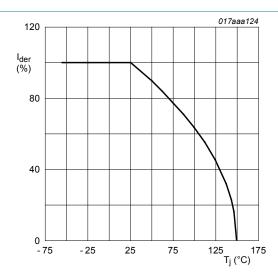


Fig. 1. Normalized total power dissipation as a function of junction temperature

$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100 \%$$



ig. 2. Normalized continuous drain current as a function of junction temperature

$$I_{der} = \frac{I_D}{I_{D(25^{\circ}C)}} \times 100 \%$$

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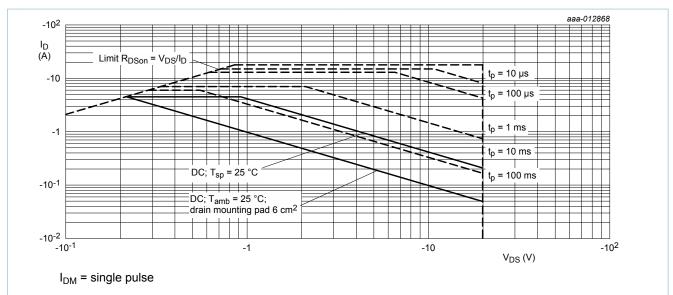


Fig. 3. Safe operating area; junction to ambient; continuous and peak drain currents as a function of drainsource voltage

Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
R _{th(j-a)}	thermal resistance from junction to ambient		[1]	-	222	255	K/W
			<u>[2]</u>	-	111	128	K/W
		in free air; t ≤ 5 s	<u>[2]</u>	-	74	85	K/W
R _{th(j-sp)}	thermal resistance from junction to solder point			-	25	30	K/W

- Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 6 cm².

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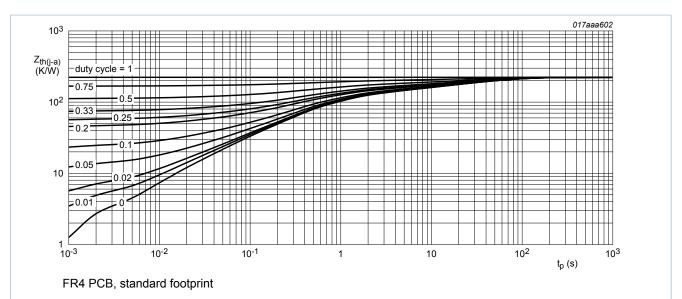


Fig. 4. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

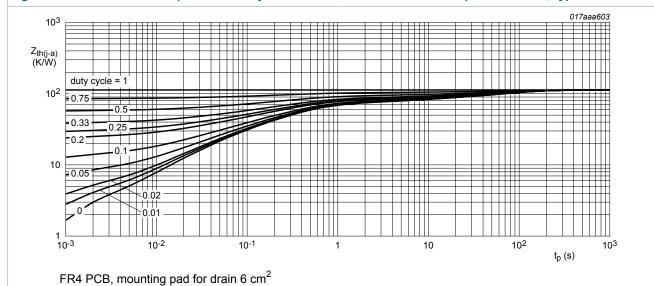


Fig. 5. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

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10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics		'			
$V_{(BR)DSS}$	drain-source breakdown voltage	$I_D = -250 \mu A; V_{GS} = 0 V; T_j = 25 °C$	-20	-	-	V
V_{GSth}	gate-source threshold voltage	I_D = -250 μ A; V_{DS} = V_{GS} ; T_j = 25 °C	-0.45	-0.7	-0.95	V
I _{DSS}	drain leakage current	V _{DS} = -20 V; V _{GS} = 0 V; T _j = 25 °C	-	-	-1	μA
I _{GSS}	gate leakage current V _G	V _{GS} = 8 V; V _{DS} = 0 V; T _j = 25 °C	-	-	10	μA
		V _{GS} = -8 V; V _{DS} = 0 V; T _j = 25 °C	-	-	-10	μA
		V _{GS} = 4.5 V; V _{DS} = 0 V; T _j = 25 °C	-	-	5	μA
		V_{GS} = -4.5 V; V_{DS} = 0 V; T_j = 25 °C	-	-	-5	μA
200	drain-source on-state	$V_{GS} = -4.5 \text{ V}; I_D = -4.5 \text{ A}; T_j = 25 \text{ °C}$	-	27	32	mΩ
	resistance	V _{GS} = -4.5 V; I _D = -4.5 A; T _j = 150 °C	-	40	48	mΩ
		V_{GS} = -2.5 V; I_D = -3.8 A; T_j = 25 °C	-	38	45	mΩ
		V_{GS} = -1.8 V; I_D = -3 A; T_j = 25 °C	-	50	63	mΩ
g _{fs}	forward transconductance	V_{DS} = -10 V; I_{D} = -2 A; T_{j} = 25 °C	-	15	-	S
R _G	gate resistance	f = 1 MHz	-	10.7	-	Ω
Dynamic ch	naracteristics					
Q _{G(tot)}	total gate charge	V_{DS} = -10 V; I_{D} = -4.4 A; V_{GS} = -4.5 V;	-	14.7	22.1	nC
Q_{GS}	gate-source charge	T _j = 25 °C	-	2.6	-	nC
Q_{GD}	gate-drain charge		-	2.5	-	nC
C _{iss}	input capacitance	V_{DS} = -10 V; f = 1 MHz; V_{GS} = 0 V;	-	1820	-	pF
C _{oss}	output capacitance	T _j = 25 °C	-	208	-	pF
C _{rss}	reverse transfer capacitance		-	146	-	pF
t _{d(on)}	turn-on delay time	V_{DS} = -10 V; I_{D} = -4.4 A; V_{GS} = -4.5 V;	-	11	-	ns
t _r	rise time	$R_{G(ext)} = 6 \Omega$; $T_j = 25 °C$	-	30	-	ns
$t_{\text{d(off)}}$	turn-off delay time		-	83	-	ns
t _f	fall time		-	39	-	ns
Source-dra	in diode		'			,
V _{SD}	source-drain voltage	$I_S = -1.2 \text{ A}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	-0.7	-1.2	V
		i l				

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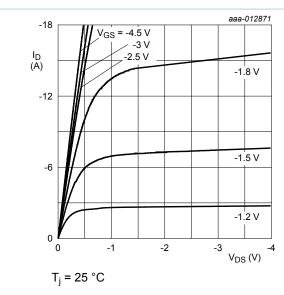


Fig. 6. Output characteristics: drain current as a function of drain-source voltage; typical values

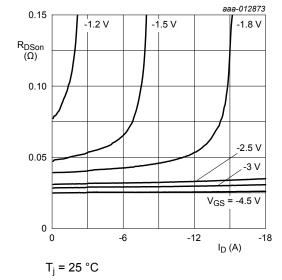


Fig. 8. Drain-source on-state resistance as a function of drain current; typical values

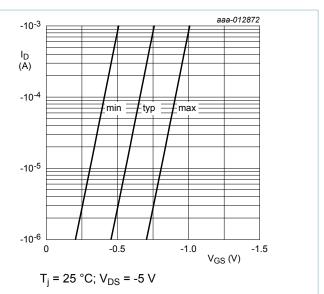


Fig. 7. Sub-threshold drain current as a function of gate-source voltage

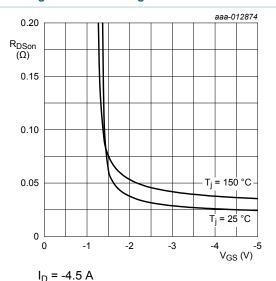


Fig. 9. Drain-source on-state resistance as a function of gate-source voltage; typical values

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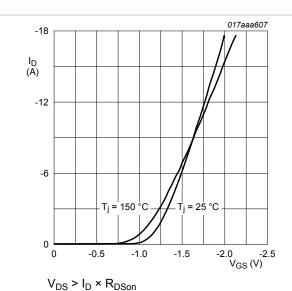


Fig. 10. Transfer characteristics: drain current as a function of gate-source voltage; typical values

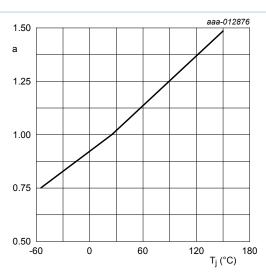


Fig. 11. Normalized drain-source on-state resistance as a function of junction temperature; typical values

$$a = \frac{R_{DSon}}{R_{DSon(25^{\circ}C)}}$$

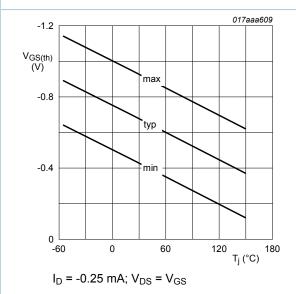
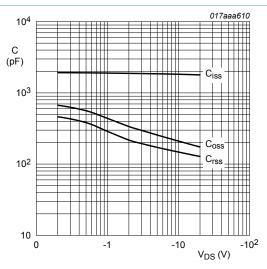


Fig. 12. Gate-source threshold voltage as a function of junction temperature



 $f = 1 MHz; V_{GS} = 0 V$

Fig. 13. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

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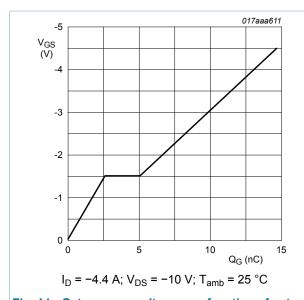


Fig. 14. Gate-source voltage as a function of gate charge; typical values

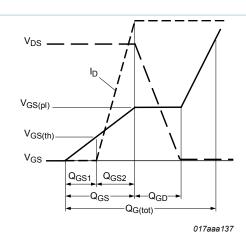


Fig. 15. MOSFET transistor: Gate charge waveform definitions

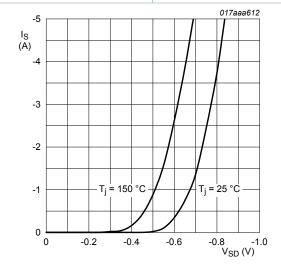
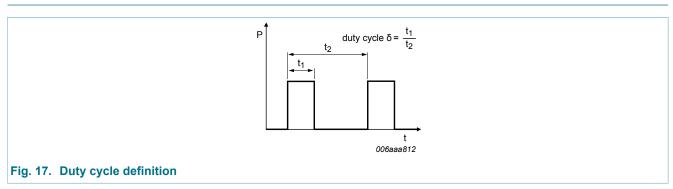


Fig. 16. Source current as a function of source-drain voltage; typical values

11. Test information

 $V_{GS} = 0 V$



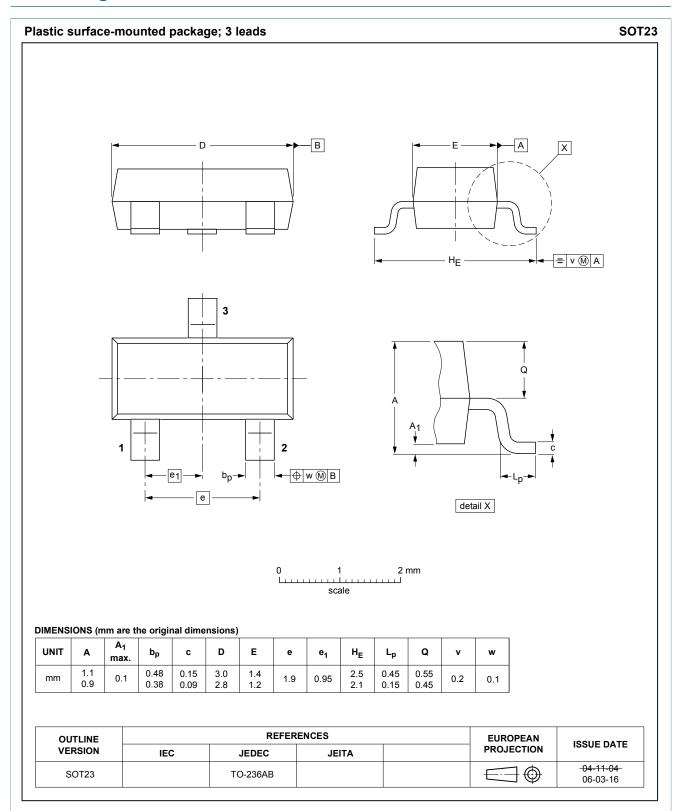
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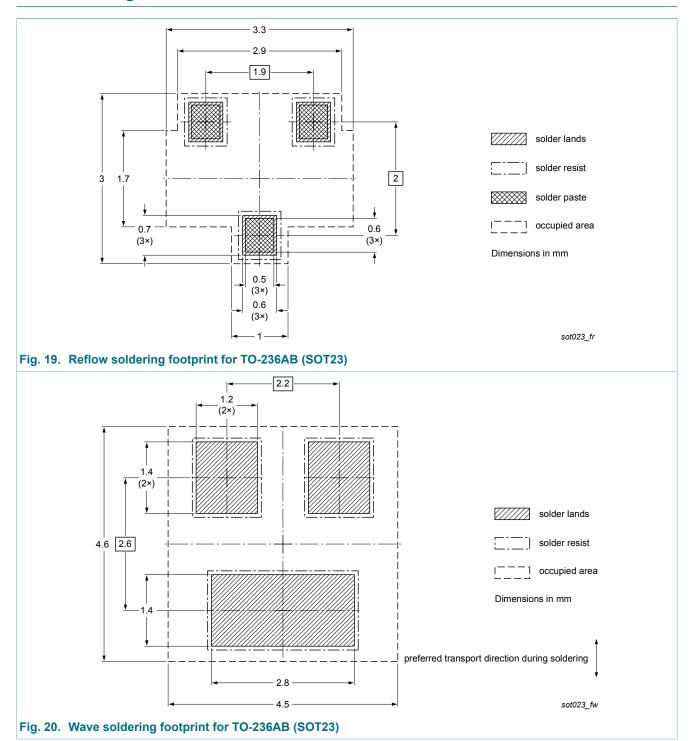
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12. Package outline



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13. Soldering



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14. Revision history

Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PMV27UPE v.1	20140515	Product data sheet	-	-

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15. Legal information

15.1 Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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Product [short] data sheet	Production	This document contains the product specification.

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